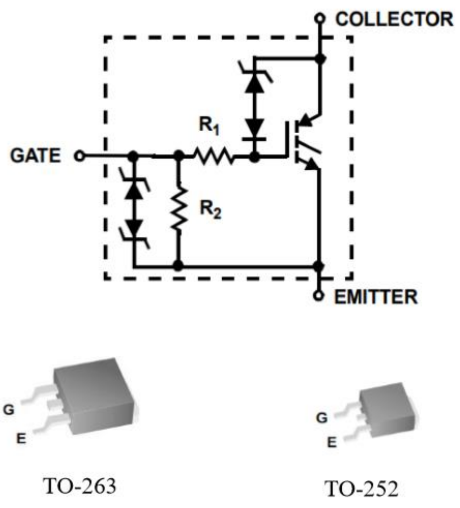
BLQG3040A

IGBT

1. Description

BLQG3040A is obtained by advanced ignition IGBTs technology which reduce the conduction loss, enhance the SCIS capability. Internally integrated diodes can provide the voltage clamping without the need for external components. The IGBT is suitable device for automotive ignition circuits, specifically as a coil driver.



KEY CHARACTERISTICS

Parameter	Value	Unit
V_{CES}	400	V
$V_{CE(sat).Typ}$	1.12	V
E_{SCIS}@T_J=25 °C	300	mJ
ESD	4	kV

FEATURES

- Low V_{CEsat}
- High SCIS Energy
- Logic Level Gate Drive
- AEC-Q101 Qualified

APPLICATIONS

- Automotive ignition Coil Driver Circuits
- Coil-On Plug Application

ORDERING INFORMATION

Ordering Codes	Product Code	Package	Device Marking	Packing
BLQG3040A-D	BLQG3040A	TO-252	QG3040A	Reel
BLQG3040A-B		TO-263		Reel

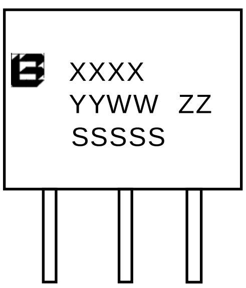
BLQG3040A-D

(2) Package type

(1) Chip name

(1) BLQG3040A: 400V 300mJ

(2) D:TO-252 B：TO-263



XXXX：Device Marking

YYWW：Year & Week

ZZ：Assembly Code

SSSSS：Lot Code

2. ABSOLUTE RATINGS

at T_C = 25°C, unless otherwise specified

Symbol	Parameter	Rating	Units
V_{CES}	Collector-Emitter Voltage	BV_{CER}	V
V_{ECS}	Emitter to Collector Voltage（I_C=10mA）	24	V
E_{SCIS}	SCIS Energy@ T_J=25 °C，I_{SCIS}=14.2A	300	mJ
	SCIS Energy@ T_J=150 °C，I_{SCIS}=10.6A	170	mJ
I_C	Collector Current @T_C=25 °C，V_{GE}=5V	35	A
	Collector Current @T_C=100 °C，V_{GE}=5V	23.8	A
ESD	Electrostatic Discharge Voltage (HBM) at 100pF,1500Ω	4	kV
V_{GEM}	Gate- Emitter Voltage Continuous	±10	V
P_D	Power Dissipation @TC = 25 °C	150	W
T_J，T_{stg}	Operating Junction and Storage Temperature Range	-40 to 175	°C
T_L	Maximum Temperature for Soldering	260	°C

3. Thermal characteristics

Symbol	Parameter	Package	RATINGS	Units
$R_{θJC}$	Junction-to-Case	TO-252/TO-263	1.0	°C/W

4. Electrical Characteristics

at T_C = 25°C, unless otherwise specified

OFF Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
BV_{CER}	Collector to Emitter Breakdown Voltage	V_{GE}=0V, I_C=2mA, R_G=1kΩ	370	400	430	V
BV_{CES}	Collector to Emitter Breakdown Voltage	V_{GE}=0V, I_C =10mA, R_G=0Ω	390	410	450	V
BV_{ECS}	Emitter to Collector Breakdown Voltage	V_{GE}=0V, I_C=-75mA	30	--	--	V
BV_{GES}	Gate to Emitter Breakdown Voltage	I_{GES}=±2mA	±12	±14		V
I_{CER}	Collector to Emitter Leakage Current	V_{CE}=250V, R_G=1kΩ, T_J=25°C	--	--	25	μA
		V_{CE}=250V, R_G=1kΩ, T_J=150°C	--	--	1	mA

I_{ECS}	Emitter to Collector Leakage Current	V_{EC}=24V, T_J=25°C	--	--	1	mA
		V_{EC}=24V, T_J=150°C			40	mA
R_1	Series Gate Resistance		--	82		Ω
R_2	Gate to Emitter Resistance		10		26	kΩ

ON Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V_{GE}=4V, I_C=6A, T_J=25°C	--	1.12	1.40	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V_{GE}=4.5V,I_C=10A,T_J=175°C	--	1.40	1.70	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V_{GE}=4.5V,I_C=15A,T_J=175°C	--	1.80	2.10	V
$V_{GE(TH)}$	Gate Threshold Voltage	V_{CE} = V_{GE}, I_C = 1mA	1.30	--	2.20	V

Pulse width tp≤300μs, δ≤2%

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	V_{GE} = 0V, V_{CE} = 25V, f=1.0MHz	--	1050	--	pF
C_{oss}	Output Capacitance		--	62	--	
C_{rss}	Reverse Transfer Capacitance		--	7.5	--	
Q_g	Total Gate Charge	I_C=10A, V_{CE}=12V, V_{GE}=5V	--	6.8	--	nC

Switching Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	V_{CE} = 14V, RL=1Ω, V_{GE} = 5V, R_G =1kΩ, T_J=25°C	--	0.5	4	μs
tr	Rise Time		--	3	7	
$t_{d(OFF)}$	Turn-Off Delay Time	V_{CE} = 300V, L=500μH, V_{GE} = 5V, R_G =1kΩ, T_J=25°C	--	5.5	15	
t_f	Fall Time		--	3	15	

5. Characteristics Curves

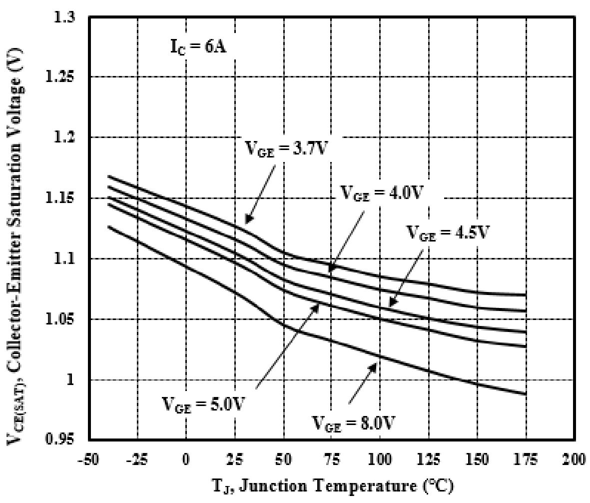
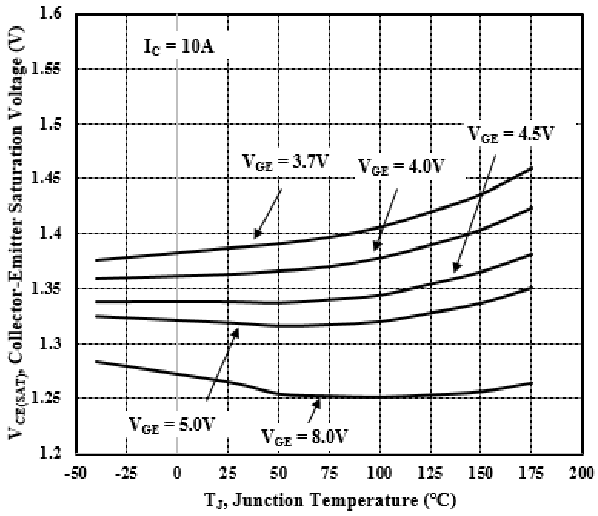
Figure 1 Collector-Emitter Saturation Voltage vs Junction Temperature	Figure 2 Collector-Emitter Saturation Voltage vs Junction Temperature
	

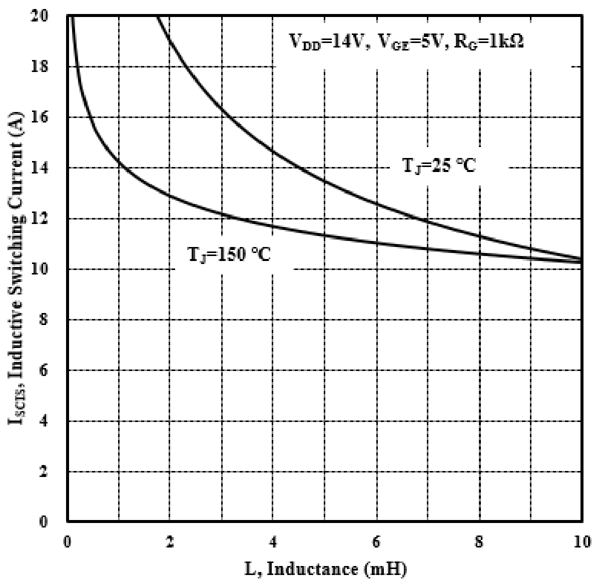
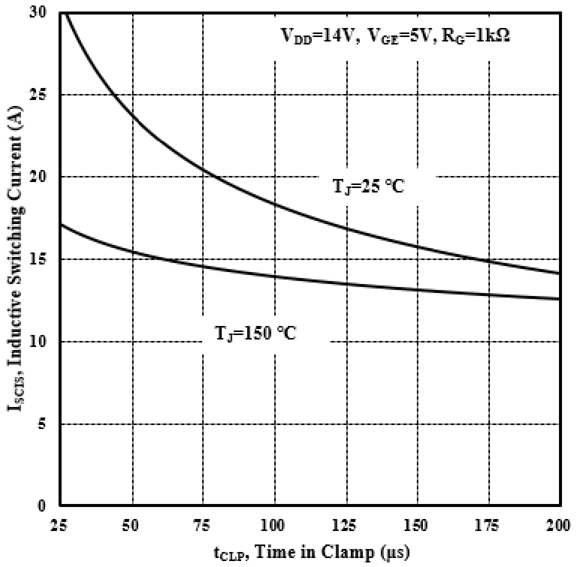
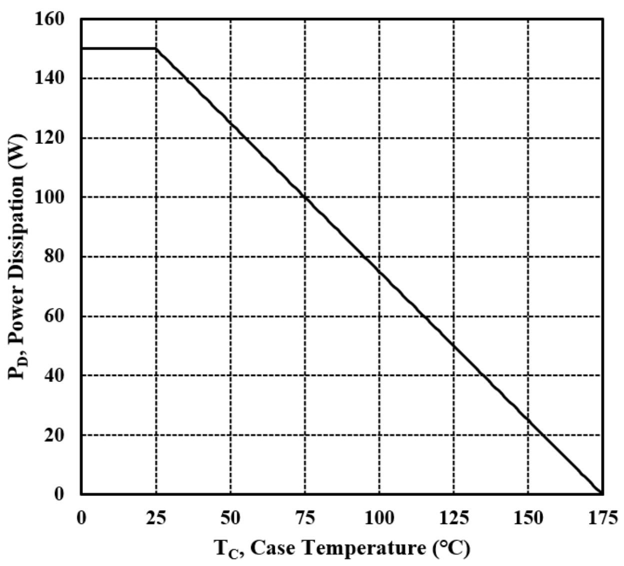
Figure 3 Self Clamped Inductive Switching Current vs Inductance	Figure 4 Self Clamped Inductive Switching Current vs Inductance
	

Figure 5 Power Dissipation vs Case Temperature	Figure 6. DC Collector Current vs Case Temperature



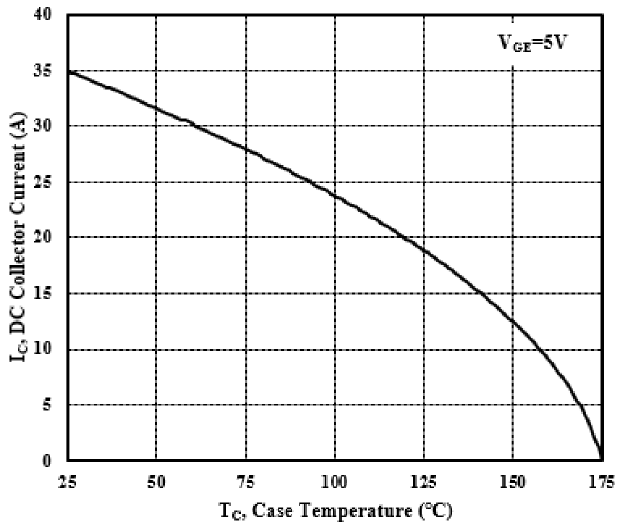
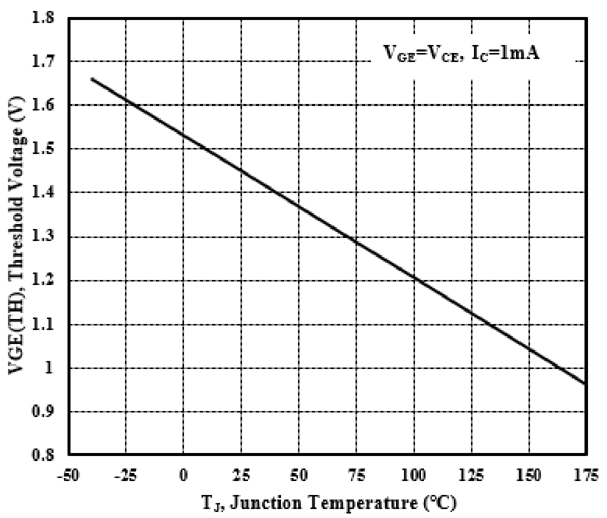


Figure 7 Threshold Voltage vs Junction Temperature	Figure 8 Breakdown Voltage vs Series Gate Resistance



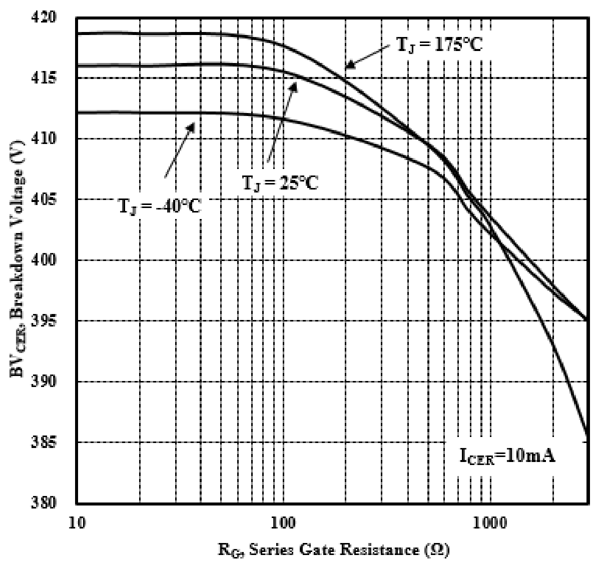


Figure 9 Leakage Current vs Junction Temperature

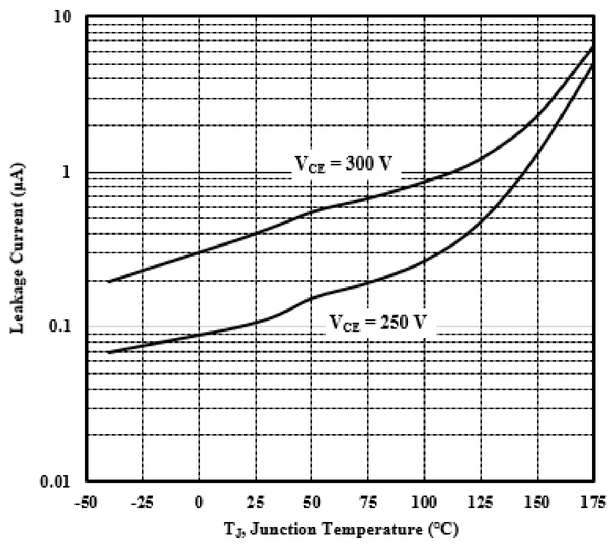


Figure 10 Collector-Emitter Voltage vs Collector Current

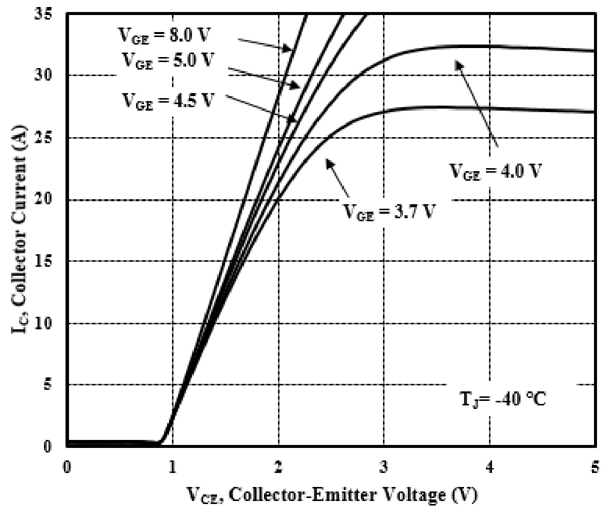


Figure 11 Collector-Emitter Voltage vs Collector Current

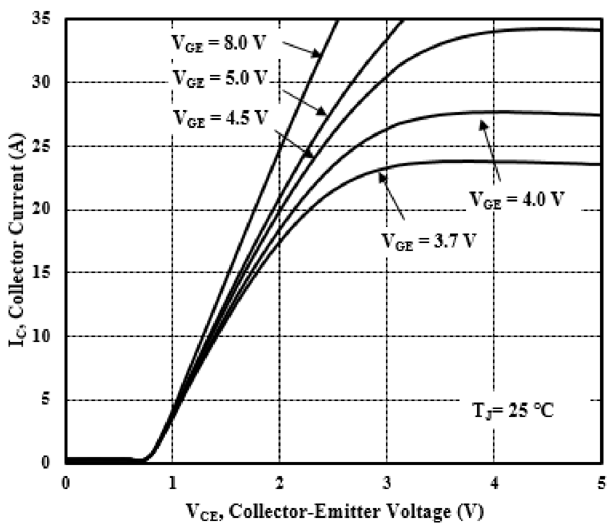


Figure 12 Collector-Emitter Voltage vs Collector Current

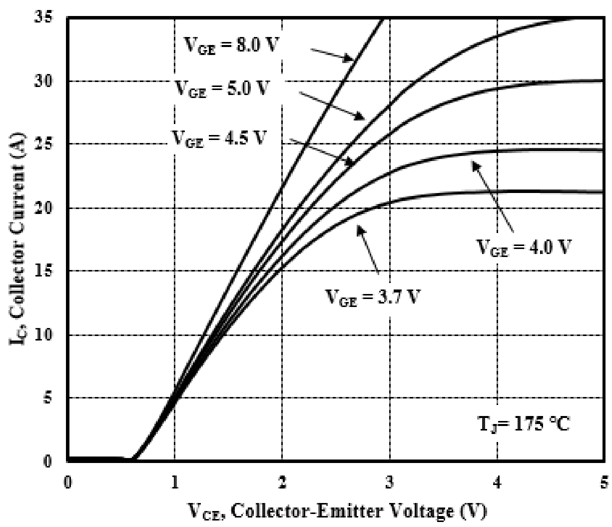


Figure 13 Transfer Characteristics

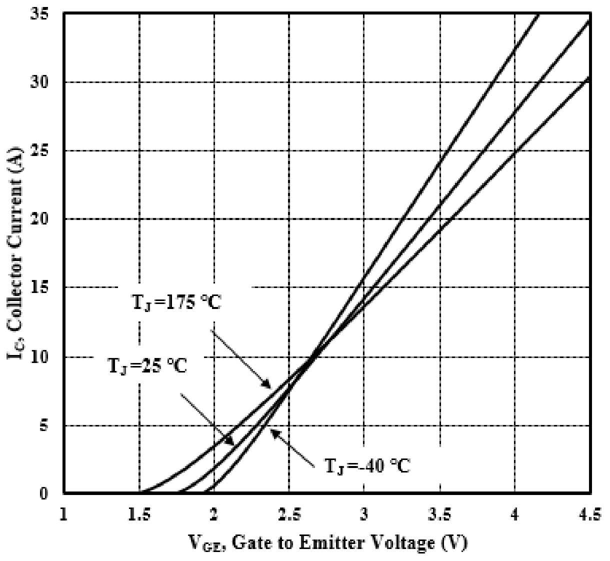


Figure 14 Capacitance vs Collector to Emitter Voltage

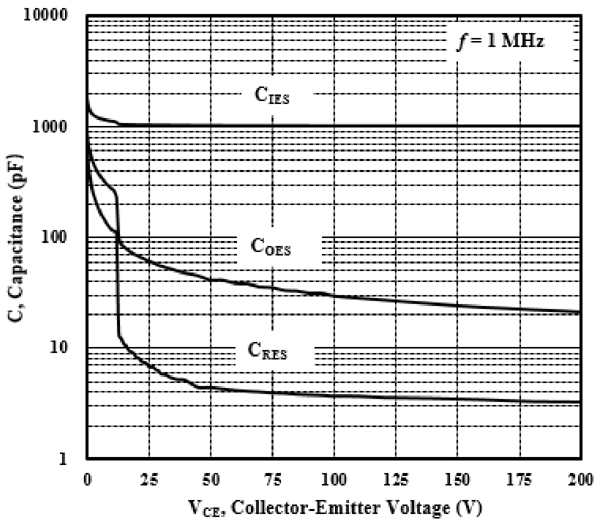


Figure 15 Gate Charge vs Gate to Emitter Voltage

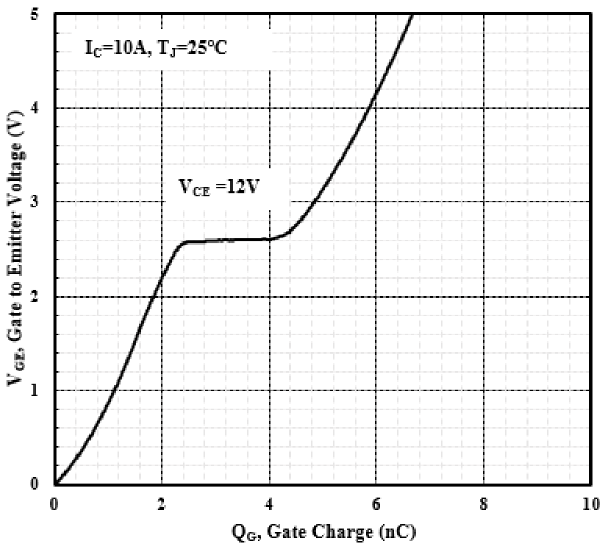


Figure 16 Switching Time vs Junction Temperature

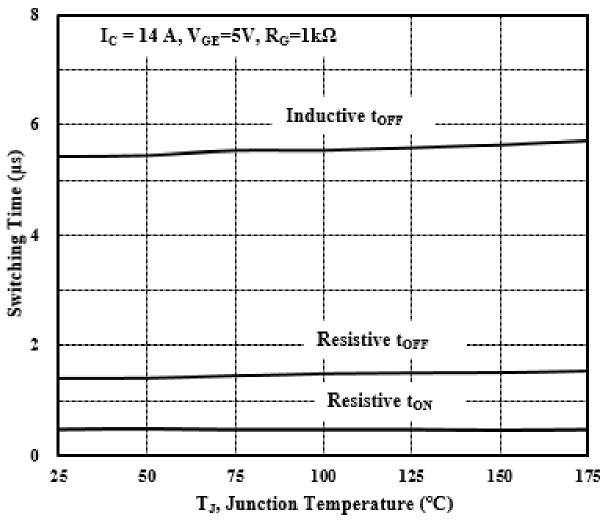
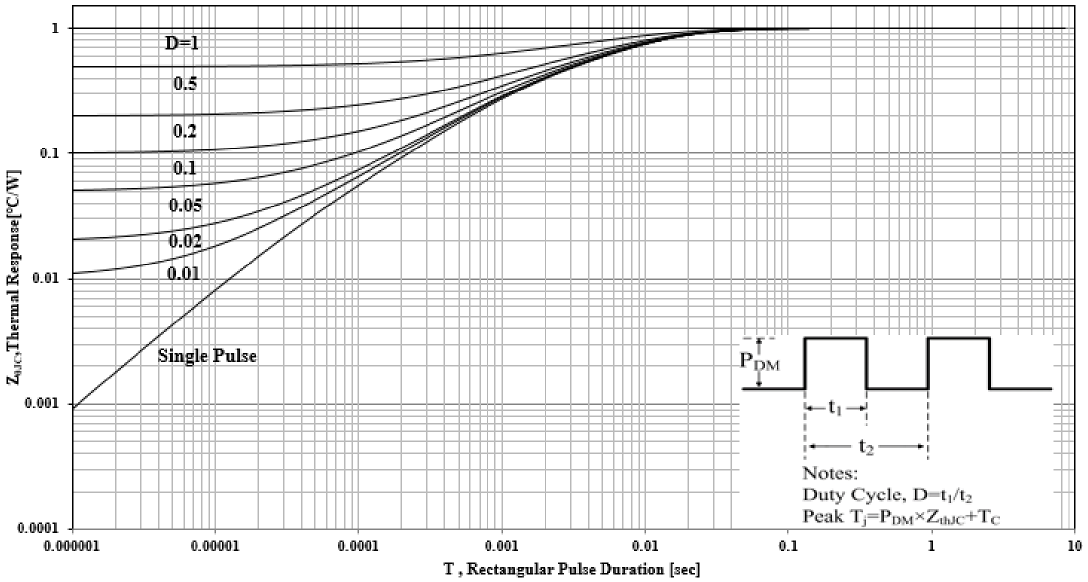


Figure 17 Transient Thermal Impedance, Junction to Case



6. Test Circuit and Waveform

Figure 18 Inductive Switching Test Circuit

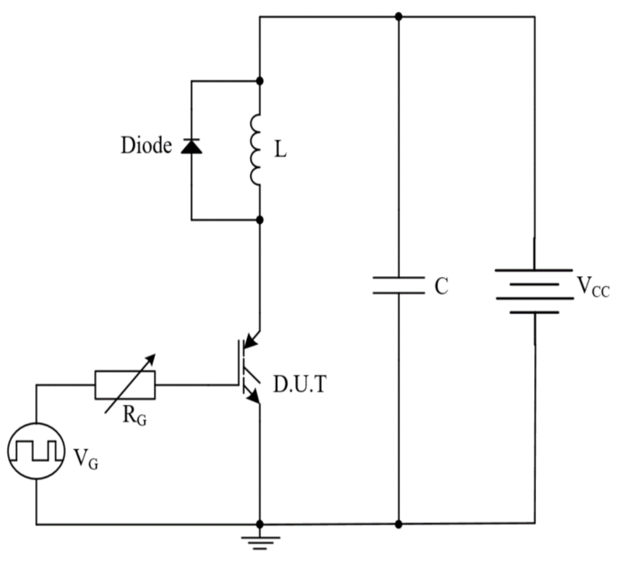


Figure 19 Resistive Switching Test Circuit

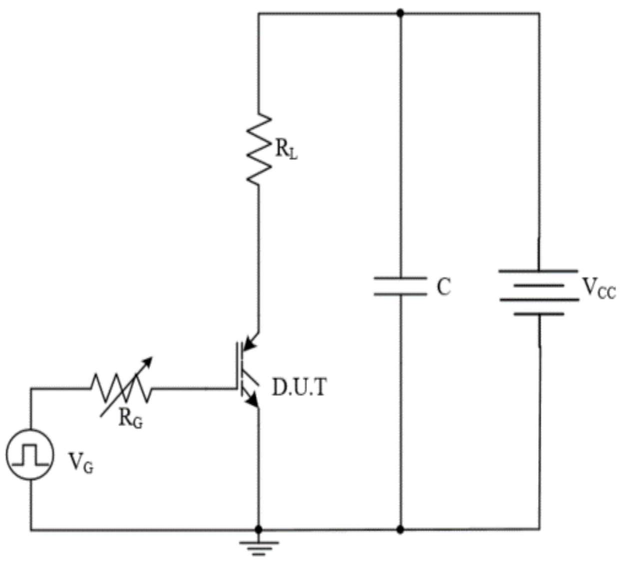


Figure 20 Switching Waveforms

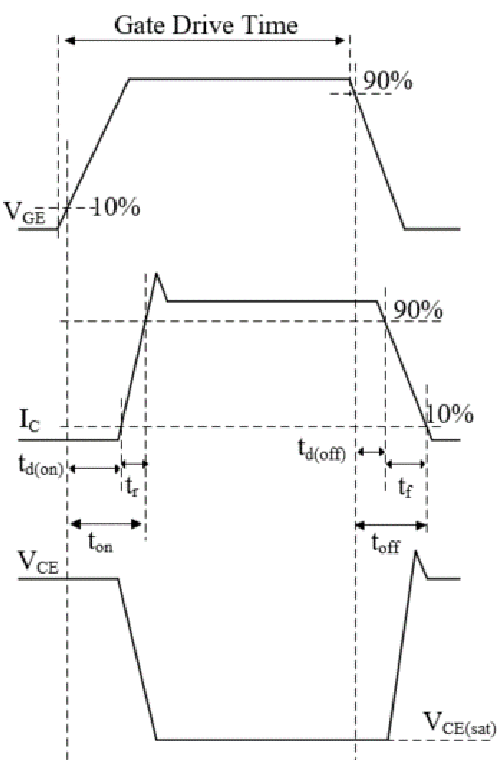


Figure 21 Self Clamped Inductive Switching Circuit

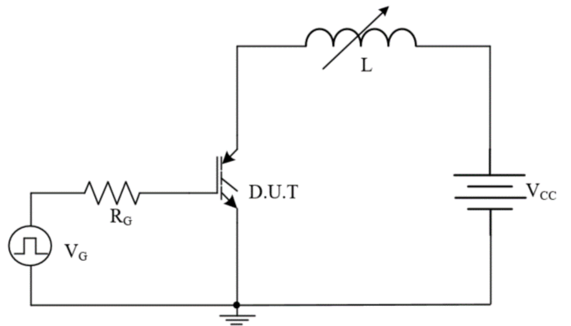
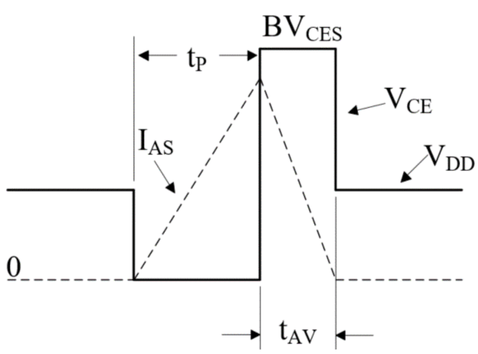
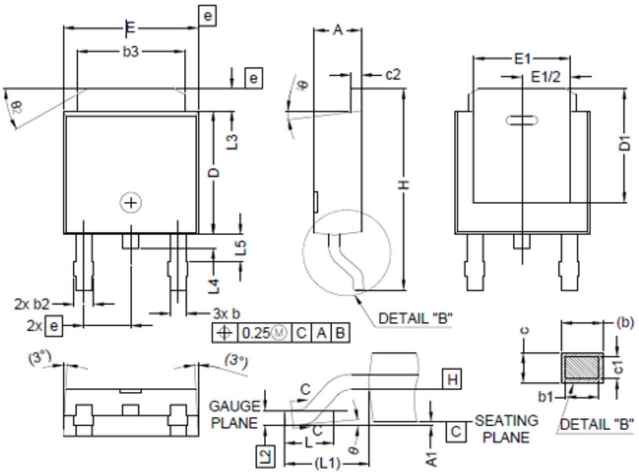


Figure 22 Self Clamped Inductive Switching Waveform

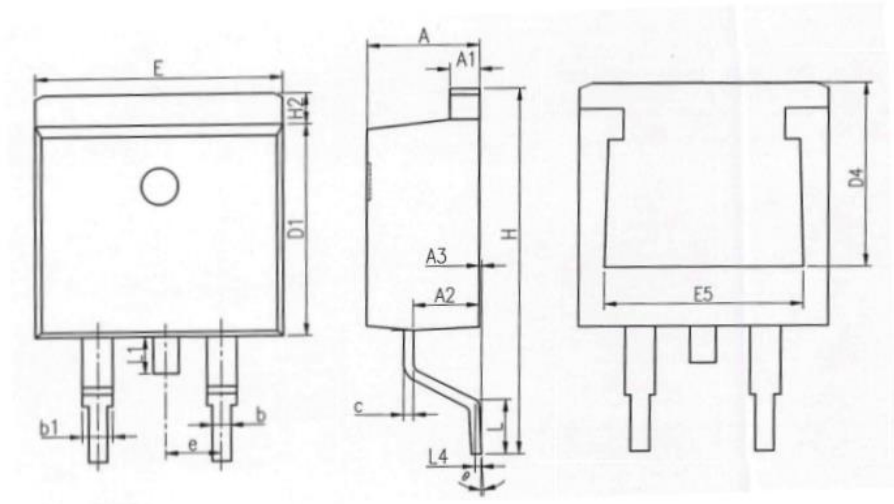


7. Package Description



TO-252 Package

Items	Values(mm)	
	MIN	MAX
A	2.18	2.39
A1	0.00	0.13
b	0.65	0.89
b1	0.64	0.79
b2	0.76	1.13
b3	4.95	5.46
c	0.46	0.61
c1	0.41	0.56
c2	0.46	0.60
D	5.97	6.22
D1	5.21	
E	6.35	6.73
E1	4.32	
e	2.29BSC	
H	9.94	10.34
L	1.50	1.78
L1	2.74REF	
L2	0.51BSC	
L3	0.89	1.27
L4		1.02
L5	1.14	1.49
θ	0°	10°
θ1	0°	15°
θ2	25°	35°



TO-263 Package

Items	Values(mm)	
	MIN	MAX
A	4.37	4.77
A1	1.22	1.42
A2	2.49	2.89
A3	0.00	0.25
b	0.70	0.96
b1	1.17	1.47
c	0.30	0.53
D1	8.5	8.9
D4	6.60	
E	9.86	10.36
E5	7.06	
e	2.54BCS	
H	14.7	15.5
H2	1.07	1.47
L	2.00	2.60
L1	1.40	1.70
L4	0.25BCS	
θ	0°	9°

Revision History:

BLQG3040A Revision: 2023-5-11, Rev. 1.0

Previous Revision

Revision	Date	Revision Date Subjects (major changes since last revision)
1.0	2023-5-11	-

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NOTE:

1. Any use beyond the maximum ratings of the device in performance may cause damage to the device or even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when designing circuit.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. Semiconductor device is sensitive to the ESD, it is necessary to protect the device from being damaged by the ESD when using it.
4. Shanghai Belling reserves the right to make changes in this specification sheet and is subject to change without prior notice.

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